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Sommario/riassunto	ZnO is a promising material for short wave-length opto-electronic devices such as UV lasers and LEDs due to its large exciton binding energy and low material cost. ZnO can be doped easily n-type, but the realization of stable p-type ZnO is rather difficult. Using first-principles band structure methods the authors address what causes the p-type doping difficulty in ZnO and how to overcome the p-type doping difficulty in ZnO.